

MUR20020

MUR200 Super Fast Recovery Diodes

Features:

- n Super fast recovery
- n Max junction temperature to 175°C
- n Low forward voltage drop

Typical Applications:

- n Inverter Welding Power Supply
- n Power Supply for Telecommunication
- n Various Switching Power Supply

$I_{F(AV)}$	200A
V_{RRM}	200V
I_{FSM}	0.8 KA
I^2t	3.2 10³A²S

CHARACTER SYSTEM	SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _J (°C)	VALUE			UNIT
					Min	Type	Max	
Rating	$I_{F(AV)}$	Mean forward current	Whole thyristor(Tc=130°C)				200	A
			Each arm(Tc=130°C)				100	
	$I_{F(RMS)}$	RMS forward current		175			314	A
	V_{RRM}	Repetitive peak reverse voltage	$V_{RRM} tp=10ms V_{RSM}= V_{RRM}+200V$	125			200	V
	I_{FRM}	Repetitive peak forward current	Each arm(rating square wave20KHz)	90			200	A
	I_{FSM}	Surge forward current	Each arm(10ms half sine wave, single pulse)	125			0.8	KA
	I^2t	I^2t value					3.2	A ² s*10 ³
T_{stg}	Storage temperature				-55	175	°C	
Heat Characteristic	$R_{th(j-c)}$	Thermal resistance junction to case	Each arm(10ms half sine wave, single side cooled)				0.45	°C /W
Electricity Characteristic	V_{FM}	Peak forward voltage	Each arm @ $I_{TM}=100A$	25			1.0	V
	I_{RRM}	Repetitive peak reverse current	$V_{RM}= V_{RRM}$	125			1000	μ A
				25			150	μ A
t_{rr}	Reverse recovery time		25			50	ns	
Mechanical Characteristic	F_m	Thermal connection torque				3.0		N·m
		Mounting torque (M6)				6.0		N·m
	W_t	Weight				80		g
	Outline	302F3						

Outline:

